



75μm InGaAs PIN PD in receptacle assembly

(P/N.: InGaAs-750-01-R)

Features

- 75μm active area
- Low dark current and high responsivity

Absolute Maximum Ratings

Parameter	Symbol	Min	Typ	Max	Unit
Operating Case Temperature	T _C	-40	-	85	°C
Storage Temperature	T _{STG}	-40	-	100	°C
Lead Soldering Temperature	T _{SOL}	-	-	260 (3s)	°C
Reverse voltage	V _R	-	-	20	V
Forward current	I _F	-	-	10	mA

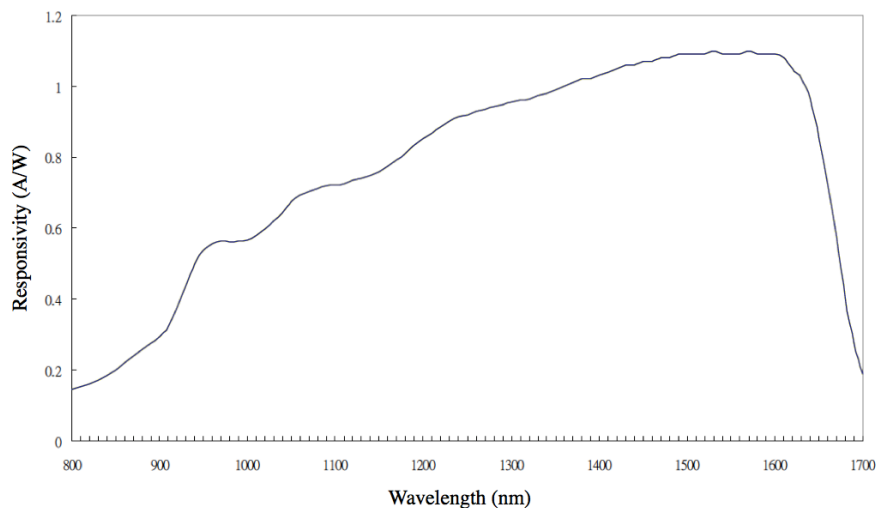
Opto-Electrical Characteristics

V_R = 5V, 25 °C

Parameter	Symbol	Min	Typ	Max	Unit
Active area	Φ	-	75	-	μm
Wavelength range	λ	900	-	1650	nm
1310nm Responsivity	R	0.8	0.85	-	A/W
1550nm Responsivity		0.85	0.9	-	A/W
Capacitance @ f = 1MHz		-	-	0.8	pF
Dark current	I _D	-	0.1	1	nA
Bandwidth	BW	2	-	-	GHz
Breakdown voltage	V _B	20	-	-	V
Saturation power	P _{SAT}	2	-	-	mW

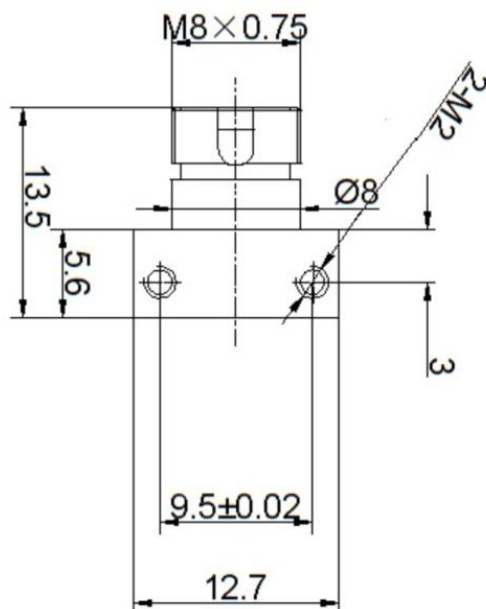
Typical Performance at 25°C

InGaAs die responsivity only

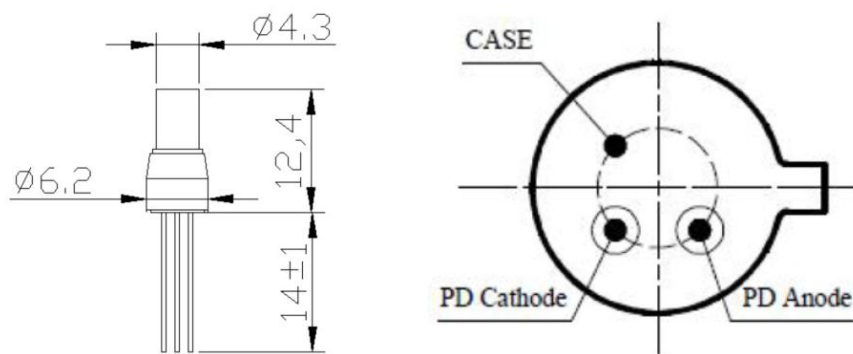


Dimensional outlines (unit = mm)

Receptacle (housing)

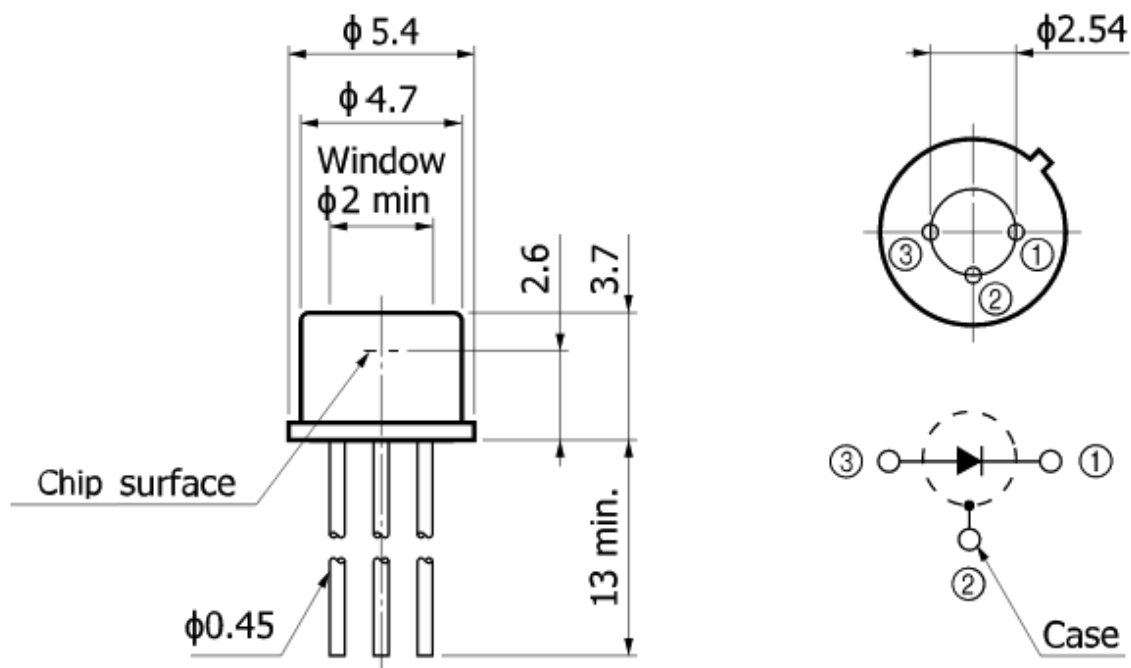


Receptacle (insert)



Package can be customized

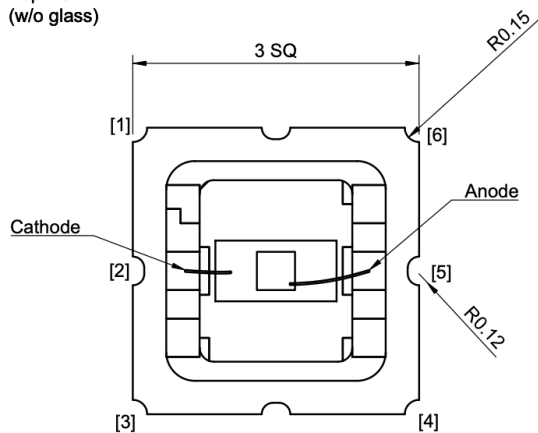
TO



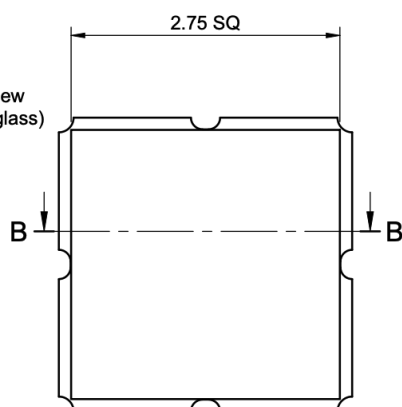
Package can be customized

SMD

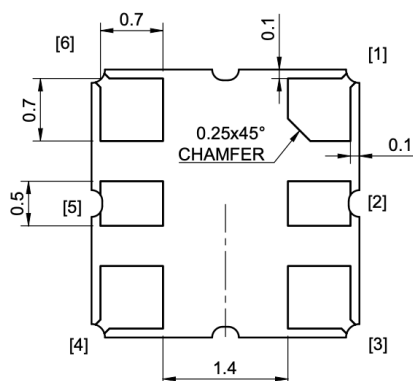
Top view
(w/o glass)



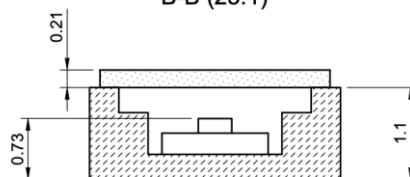
Top view
(with glass)



Bottom view



B-B (25:1)



Package can be customized